

**GaAs SPDT Switch
DC - 3.0 GHz**

**MASWSS0166
V2**

Features

- Low Insertion Loss: 0.3 dB @ 900 MHz
- Low Current Consumption: <15 μ A @ +2.5 V
- Positive or Negative 2.5 to 8 V Control
- Lead-Free SOT-363 Package
- 100% Matte Tin Plating over Copper
- Halogen-Free "Green" Mold Compound
- 260°C Reflow Compatible
- RoHS* Compliant Version of SW-437

Description

M/A-COM's MASWSS0166 is a GaAs monolithic switch in a lead-free SOT-363 surface mount plastic package. The MASWSS0166 is ideally suited for applications where very low power consumption, low insertion loss, very small size and low cost are required.

Typical applications are dual band systems that require switching between small signal components such as filter banks, single band LNA's and converters. The MASWSS0166 can be used in applications up to 0.25 Watts in systems such as cellular, PCS, DCS1800, GSM, CDMA, W-CDMA and other analog/digital wireless communications systems.

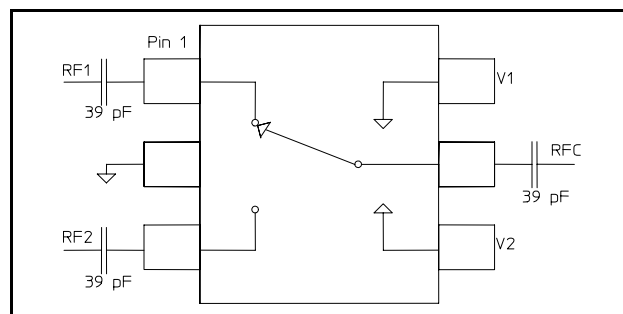
The MASWSS0166 is fabricated using a mature 0.5 micron GaAs PHEMT process. The process features full passivation for increased performance and reliability.

Absolute Maximum Ratings ^{1,2}

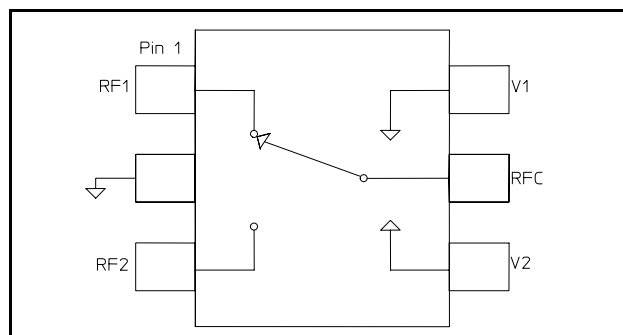
Parameter	Absolute Maximum
Input Power (0.5-3.0 GHz) 3 V Control 5 V Control	+30 dBm +33 dBm
Operating Voltage	+8.5 Volts
Operating Temperature	-40°C to +85°C
Storage Temperature	-65°C to +150°C

1. Exceeding any one or combination of these limits may cause permanent damage to this device.
2. M/A-COM does not recommend sustained operation near these survivability limits.

**Functional Schematic
Positive Control Voltage**



**Functional Schematic
Negative Control Voltage**



Pin Configuration

Pin No.	Function	Description
1	RF1	RF in/out
2	GND	RF Ground
3	RF2	RF in/out
4	V2	V Control 2
5	RFC	RF Common
6	V1	V Control 1

Ordering Information

Part Number	Package
MASWSS0166	Bulk Packaging
MASWSS0166TR-3000	3000 piece reel
MASWSS0166SMB	Sample Test Board

Note: Reference Application Note M513 for reel size information.

* Restrictions on Hazardous Substances, European Union Directive 2002/95/EC.

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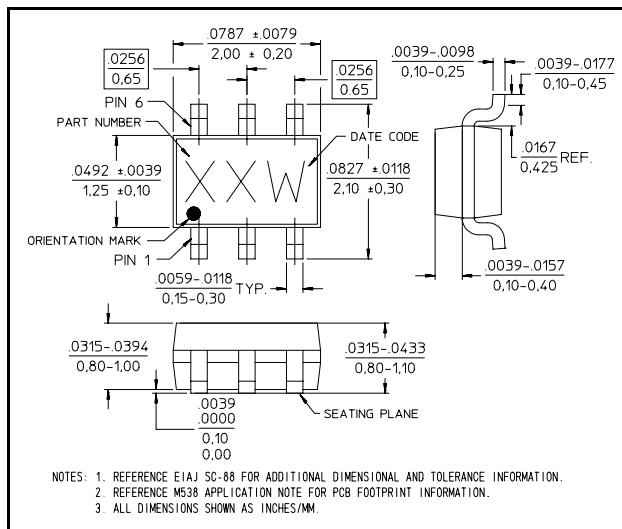
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Electrical Specifications: $T_A = 25^\circ\text{C}$, $V_c = 0\text{ V} / -2.5\text{ V}$, $Z_0 = 50\Omega^3$

Parameter	Test Conditions	Units	Min.	Typ.	Max.
Insertion Loss	DC - 1 GHz	dB	—	0.3	0.4
	1 - 2 GHz	dB	—	0.4	0.5
	2 - 3 GHz	dB	—	0.55	0.7
Isolation	DC - 1 GHz	dB	19	21	—
	1 - 2 GHz	dB	13	15	—
	2 - 3 GHz	dB	10	12	—
VSWR	DC - 3 GHz	Ratio	—	1.2:1	—
P_{1dB}	500 MHz - 3 GHz, $ V_c = 2.7\text{ V}$	dBm	—	24	—
P_{1dB}	500 MHz - 3 GHz, $ V_c = 5\text{ V}$	dBm	—	27	—
Input IP_2	2-Tone, 900 MHz, 5 MHz spacing, $ V_c = 2.7\text{ V}$	dBm	—	81	—
Input IP_3	2-Tone 900 MHz, 5 MHz spacing, $ V_c = 2.7\text{ V}$	dBm	—	55	—
Trise, Tfall Ton, Toff Transients	10% to 90% RF, 90% to 10% RF 50% Control to 90% RF, 50% Control to 10% RF In-Band	nS nS mV	— — —	10 20 10	— — —
Control Current	$ V_c = 2.5\text{ V}$	μA	—	4	15

3. For positive voltage control, external DC blocking capacitors are required on all RF ports.

Lead-Free SOT-363 Plastic Package[†]



[†] Reference Application Note M538 for lead-free solder reflow recommendations.

Truth Table^{4,5}

V1	V2	RFC-RF1	RFC-RF2
0	1	On	Off
1	0	Off	On

4. Differential voltage, $V(\text{state } 1) - V(\text{state } 0)$, must be +2.5 V minimum and must not exceed 8 V.
5. 0 = -8 V to 0 V, 1 = -5.5 V to 8 V

Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

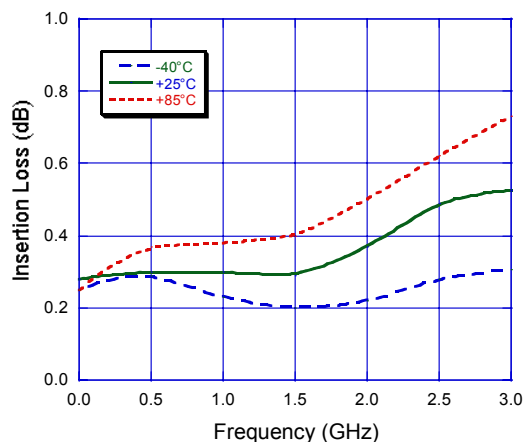
Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

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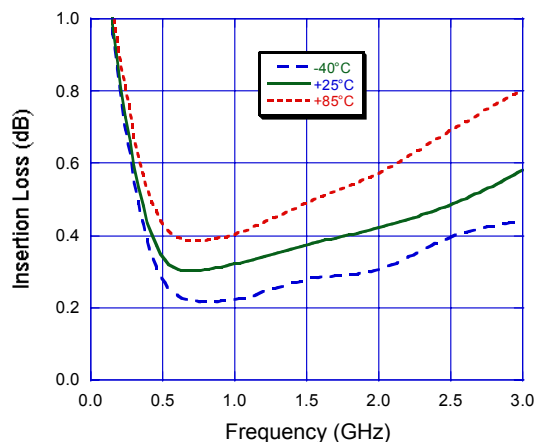
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Typical Performance Curves

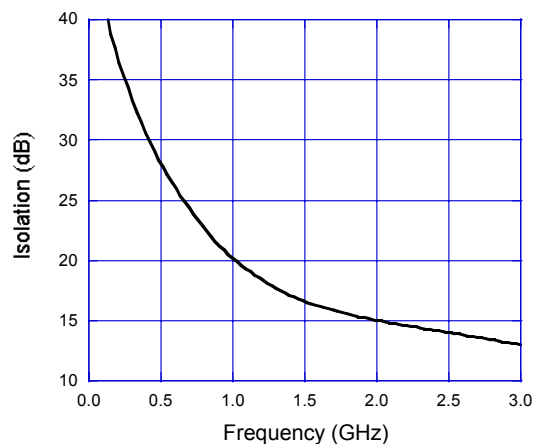
Insertion Loss (Negative Voltage Control)



Insertion Loss (Positive Voltage Control)



Isolation



VSWR

